

MOS FIELD EFFECT TRANSISTOR  
NP88N04CHE, NP88N04DHE, NP88N04EHE

SWITCHING  
N-CHANNEL POWER MOS FET  
INDUSTRIAL USE

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance  
 $R_{DS(on)} = 4.3 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 44 \text{ A)}$
- Low  $C_{iss}$  :  $C_{iss} = 7300 \text{ pF TYP.}$
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage	$V_{DSS}$	40	V
Gate to Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (DC) <sup>Note1</sup>	$I_{D(DC)}$	$\pm 88$	A
Drain Current (Pulse) <sup>Note2</sup>	$I_{D(pulse)}$	$\pm 352$	A
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_T$	1.8	W
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_T$	288	W
Single Avalanche Current <sup>Note3</sup>	$I_{AS}$	75 / 88	A
Single Avalanche Energy <sup>Note3</sup>	$E_{AS}$	562 / 232	mJ
Channel Temperature	$T_{ch}$	175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$

- ★ **Notes** 1. Calculated constant current according to MAX. allowable channel temperature.  
 2.  $PW \leq 10 \mu\text{s}$ , Duty cycle  $\leq 1 \%$   
 3. Starting  $T_{ch} = 25 \text{ }^\circ\text{C}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$  (see Figure 4.)

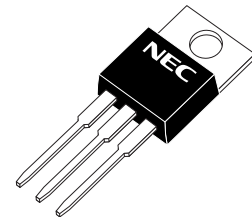
THERMAL RESISTANCE

Channel to Case	$R_{th(ch-C)}$	0.52	$^\circ\text{C/W}$
Channel to Ambient	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

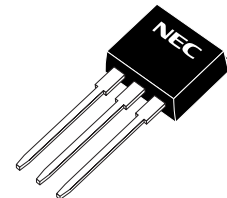
ORDERING INFORMATION

PART NUMBER	PACKAGE
NP88N04CHE	TO-220AB
NP88N04DHE	TO-262
NP88N04EHE	TO-263

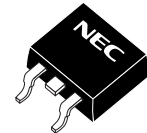
(TO-220AB)



(TO-262)



(TO-263)

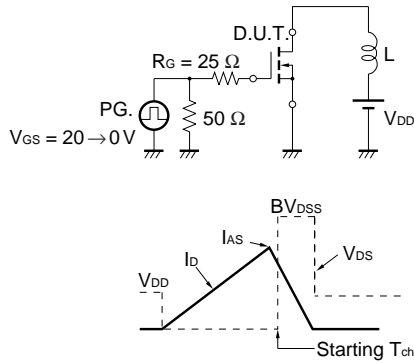


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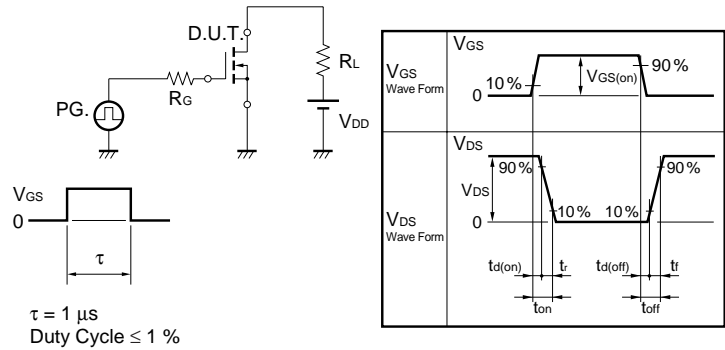
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 44 A		3.4	4.3	mΩ
Gate to Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	3.0	4.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 44 A	30	60		S
Drain Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V			10	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V		7300	11000	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		1400	2100	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		620	1120	pF
★ Turn-on Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 44 A		38	84	ns
★ Rise Time	t <sub>r</sub>	V <sub>GS(on)</sub> = 10 V		27	68	ns
★ Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>DD</sub> = 20 V		110	220	ns
★ Fall Time	t <sub>f</sub>	R <sub>G</sub> = 1 Ω		32	80	ns
Total Gate Charge	Q <sub>G</sub>	I <sub>D</sub> = 88 A		120	180	nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>DD</sub> = 32 V		30		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> = 10 V		43		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 88 A, V <sub>GS</sub> = 0 V		0.95		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 88 A, V <sub>GS</sub> = 0 V		64		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		99		nC

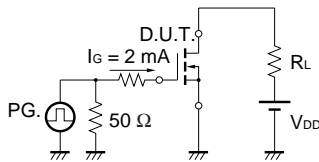
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**



**TEST CIRCUIT 3 GATE CHARGE**



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Figure1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

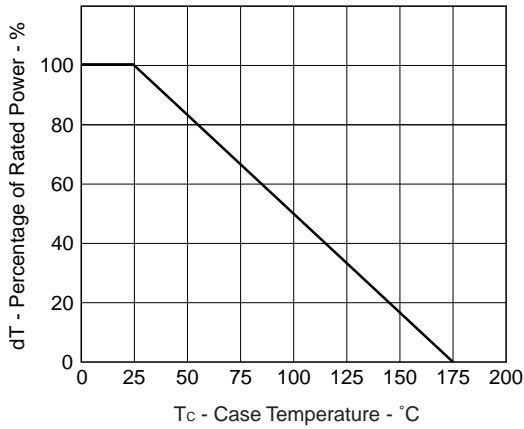


Figure2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

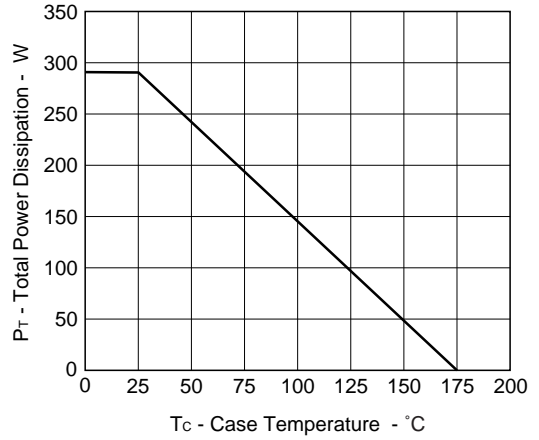


Figure3. FORWARD BIAS SAFE OPERATING AREA

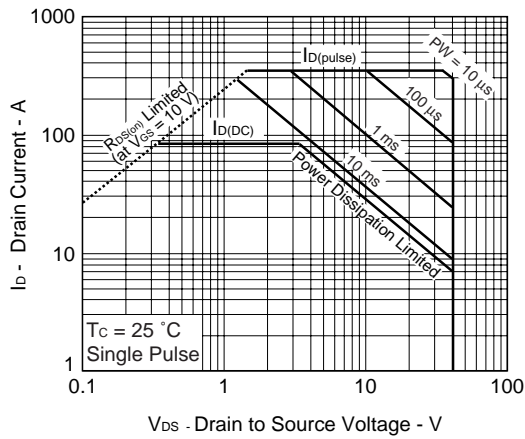


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

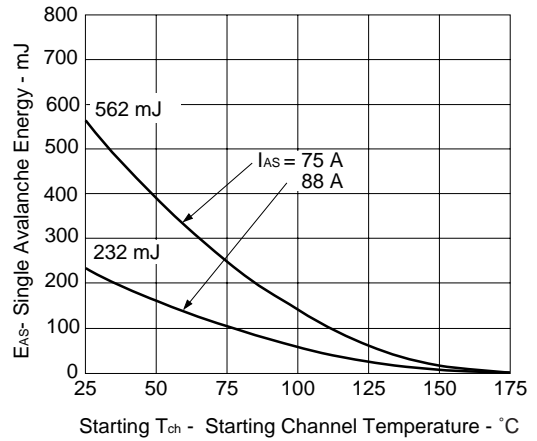


Figure5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

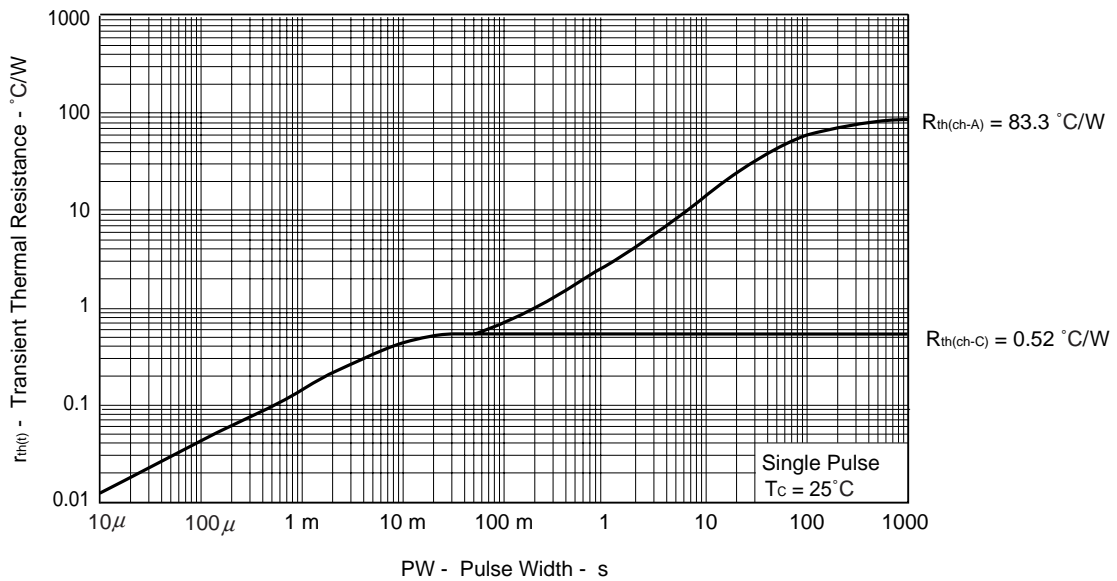


Figure6. FORWARD TRANSFER CHARACTERISTICS

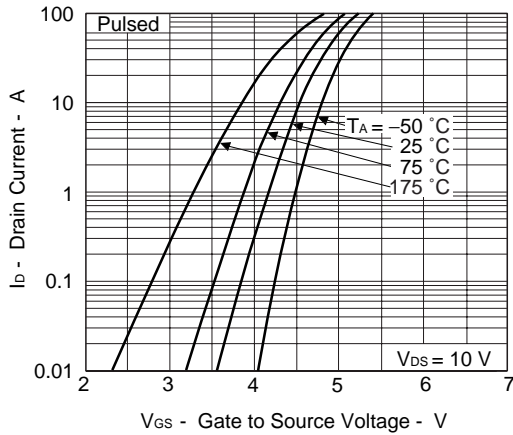


Figure7. DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

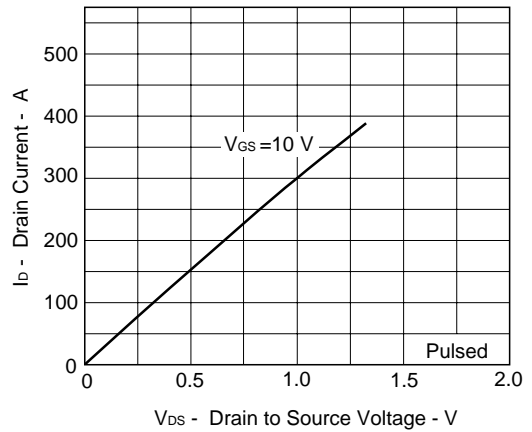


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

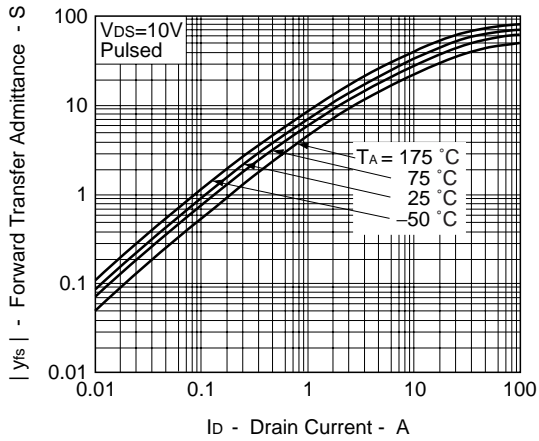


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

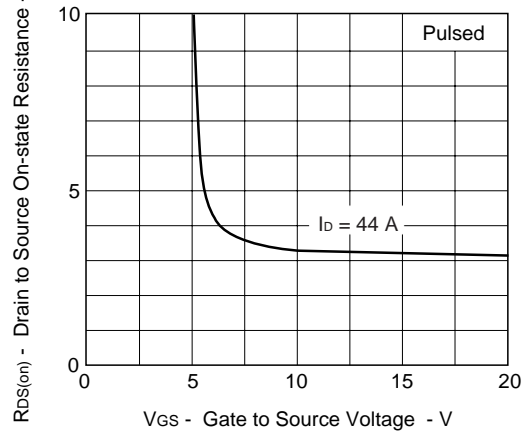


Figure10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

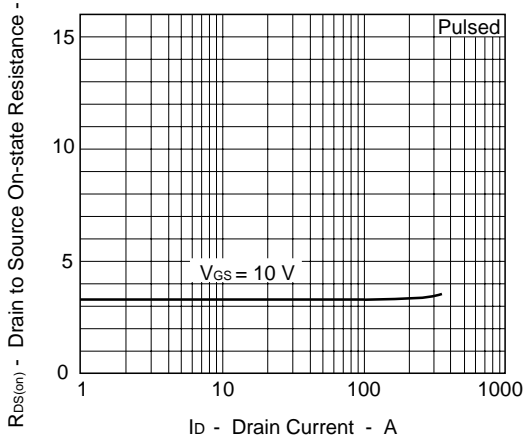


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

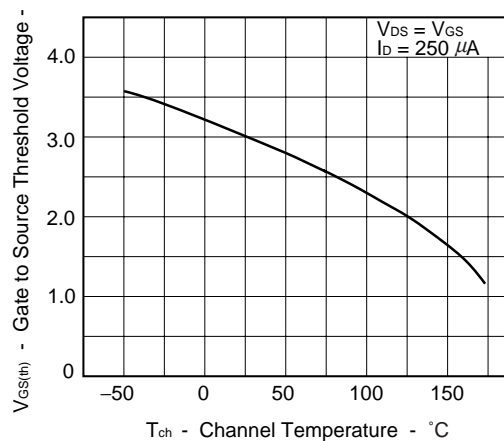


Figure12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

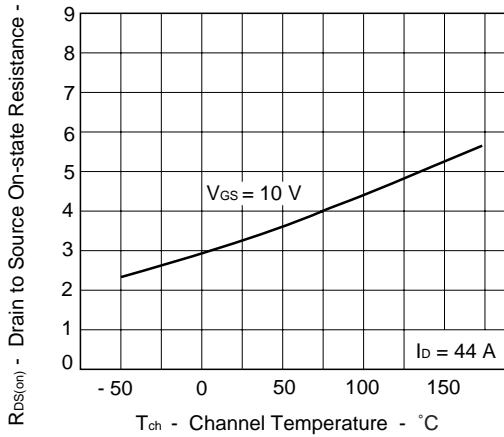


Figure13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

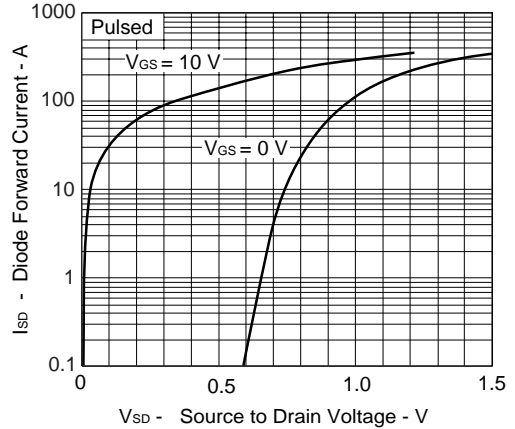
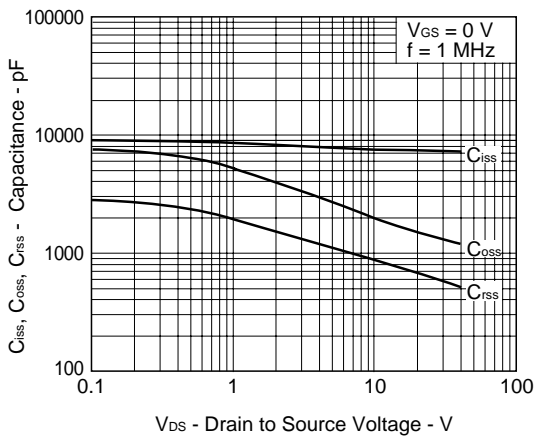


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



★ Figure15. SWITCHING CHARACTERISTICS

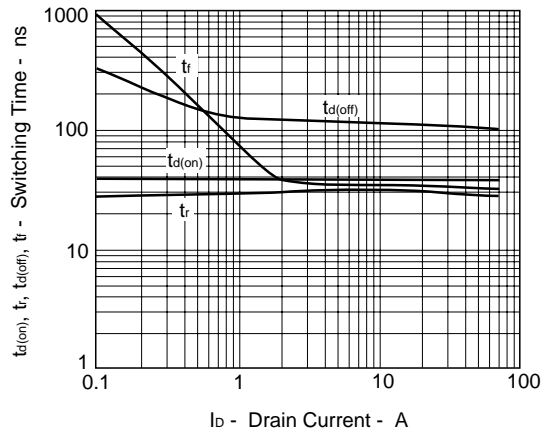


Figure16. REVERSE RECOVERY TIME vs. DRAIN CURRENT

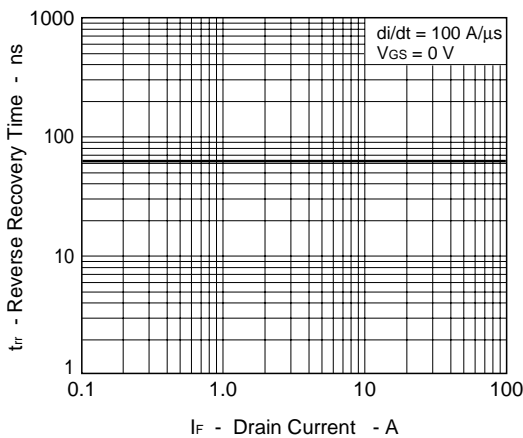
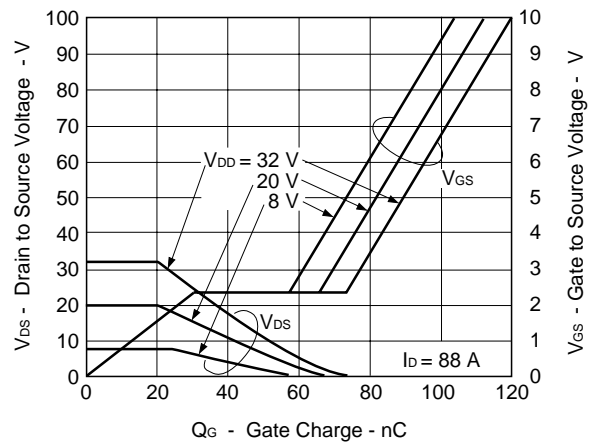
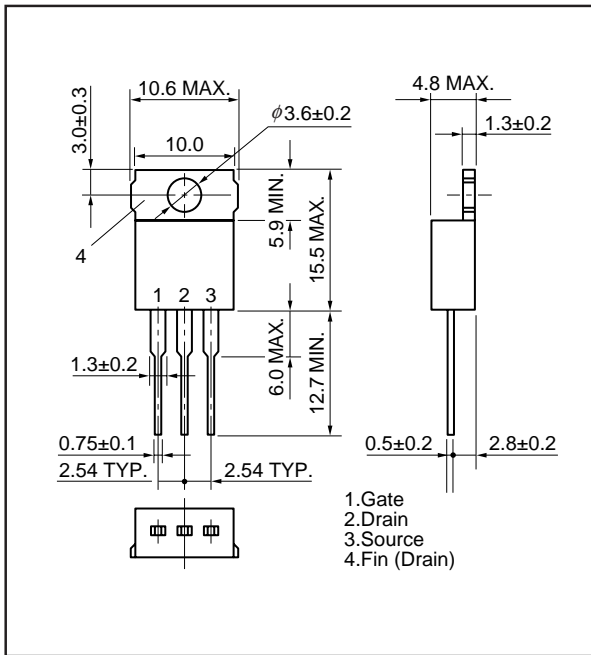


Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

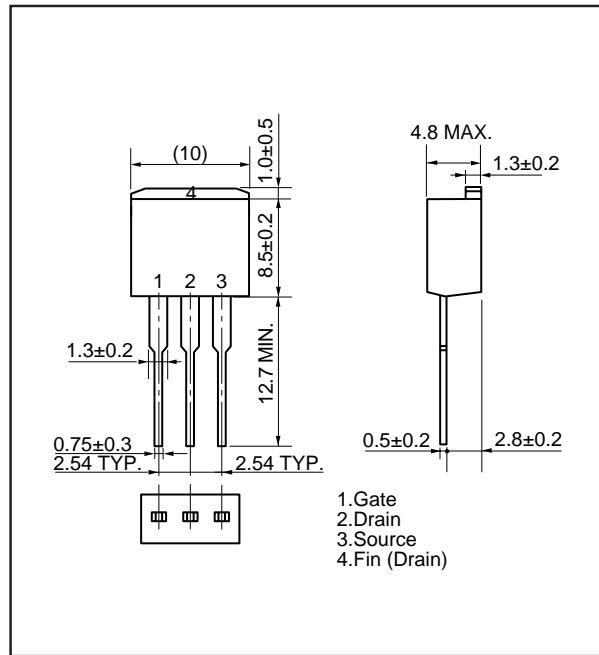


PACKAGE DRAWINGS (Unit: mm)

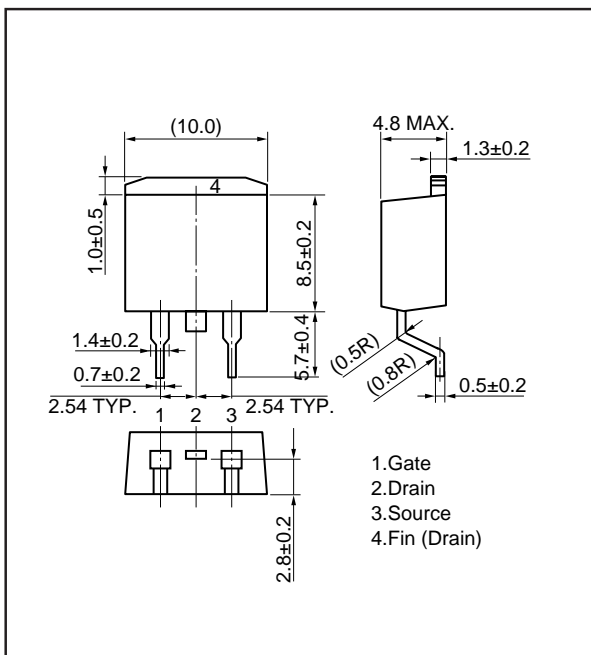
1) TO-220AB (MP-25)



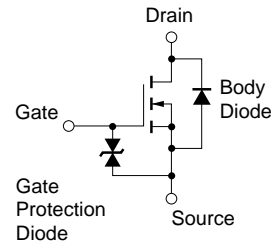
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

[MEMO]

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